



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





# ACTT4X-800E

## AC Thyristor Triac power switch

15 August 2014

Product data sheet

### 1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

### 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Isolated mounting base package
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$

### 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

### 4. Quick reference data

Table 1. Quick reference data

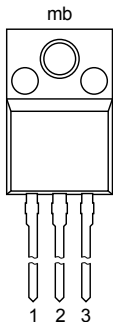
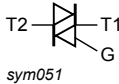
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	35	A
$T_j$	junction temperature		-	-	125	$^{\circ}\text{C}$
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_n \leq 94\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	4	A



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>PP</sub>	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	-	2	kV
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	10	mA
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>	500	-	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 1 V/μs; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220F (SOT186A)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

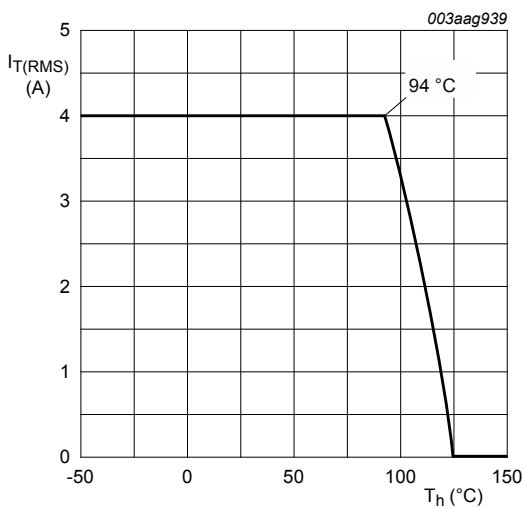
Type number	Package		
	Name	Description	Version
ACTT4X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 7. Limiting values

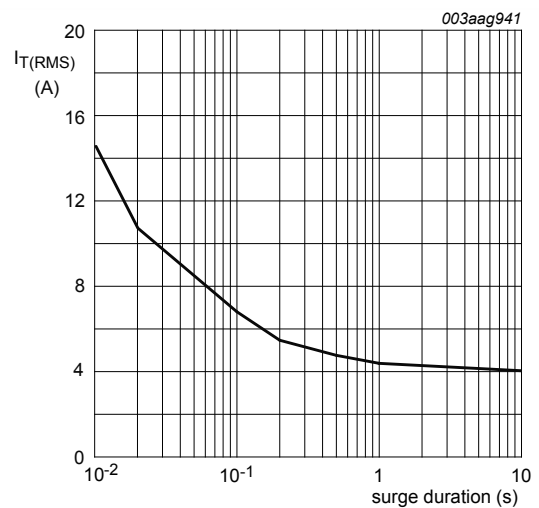
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 94\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	4	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	35	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	39	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	6	$A^2s$
$di_T/dt$	rate of rise of on-state current	$I_T = 6\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu s$	-	100	$A/\mu s$
$I_{GM}$	peak gate current	$t = 20\text{ }\mu s$	-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}C$
$T_j$	junction temperature		-	125	$^{\circ}C$
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ °C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	2	kV



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_h = 94\text{ °C}$

**Fig. 2. on-state current as a function of surge duration; maximum values**

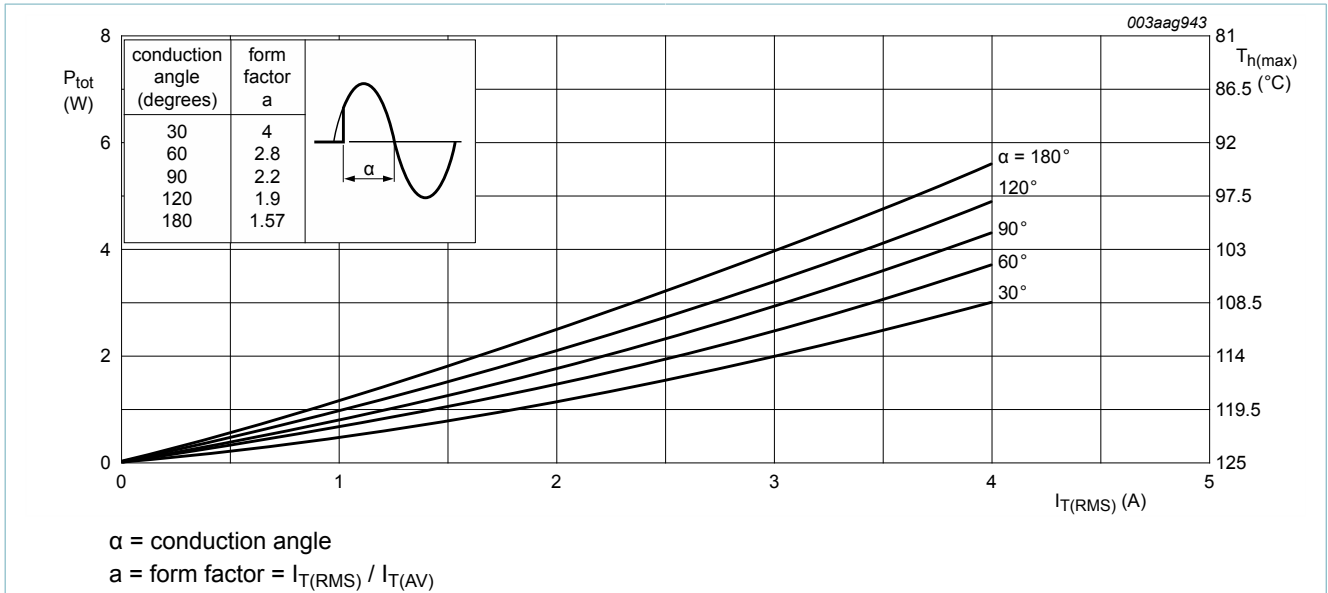


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

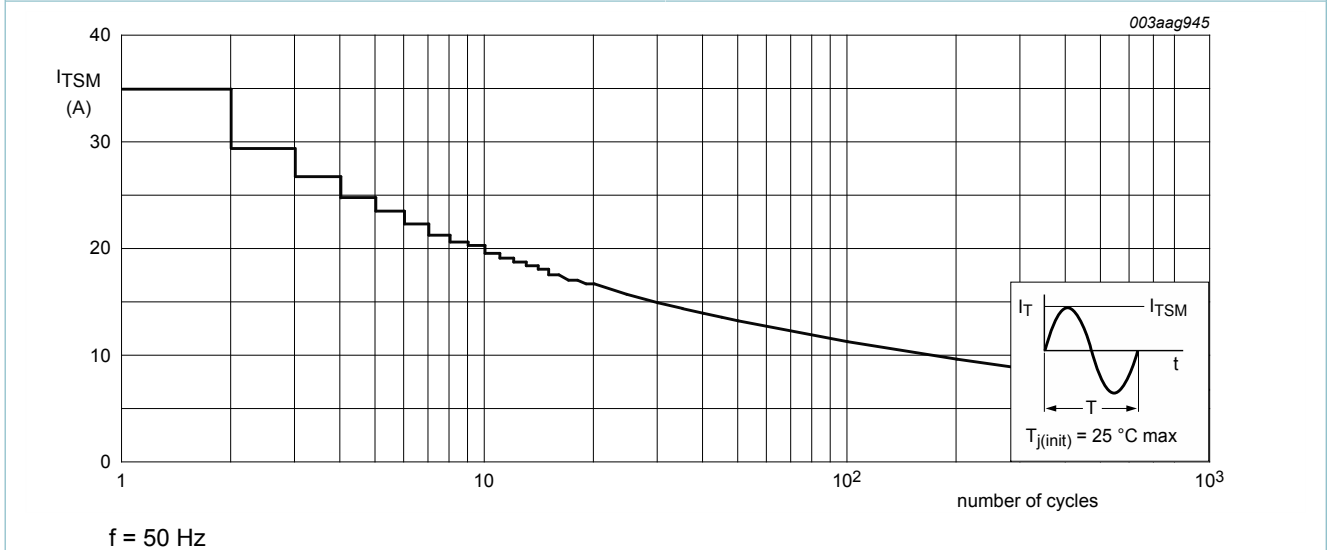


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

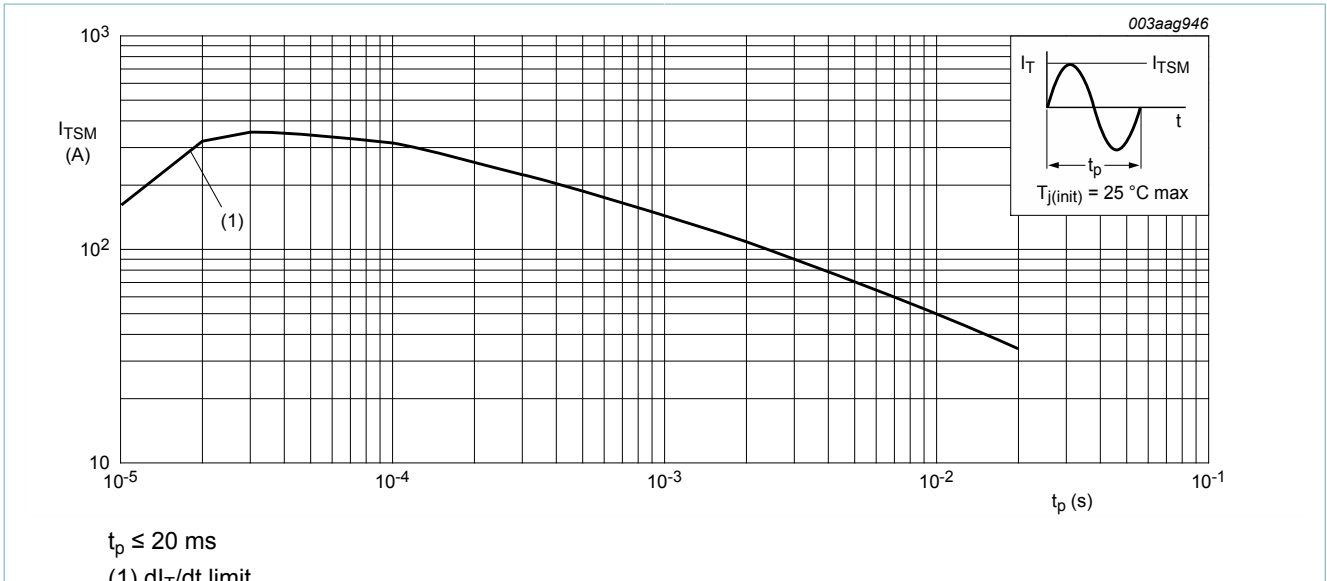


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

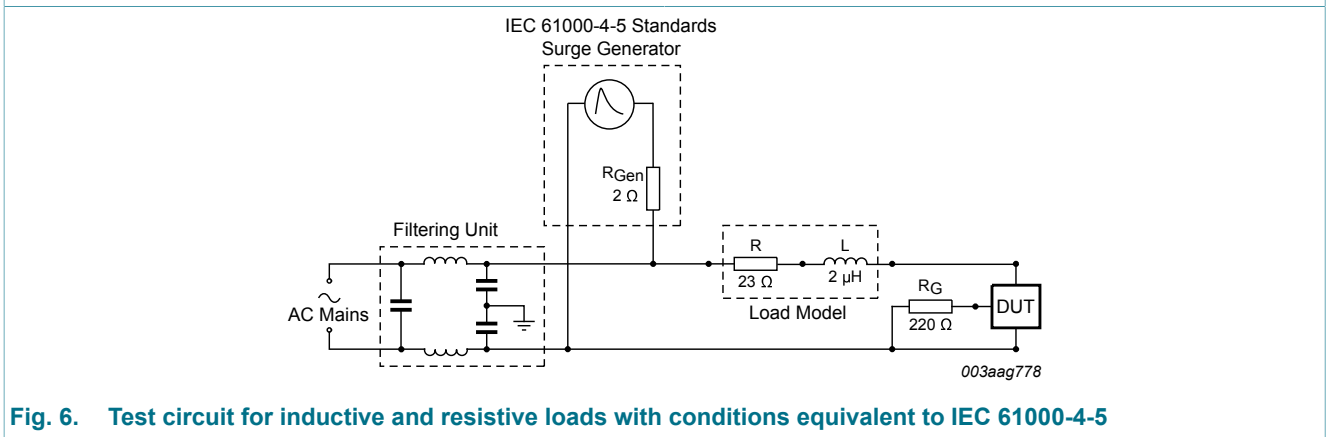
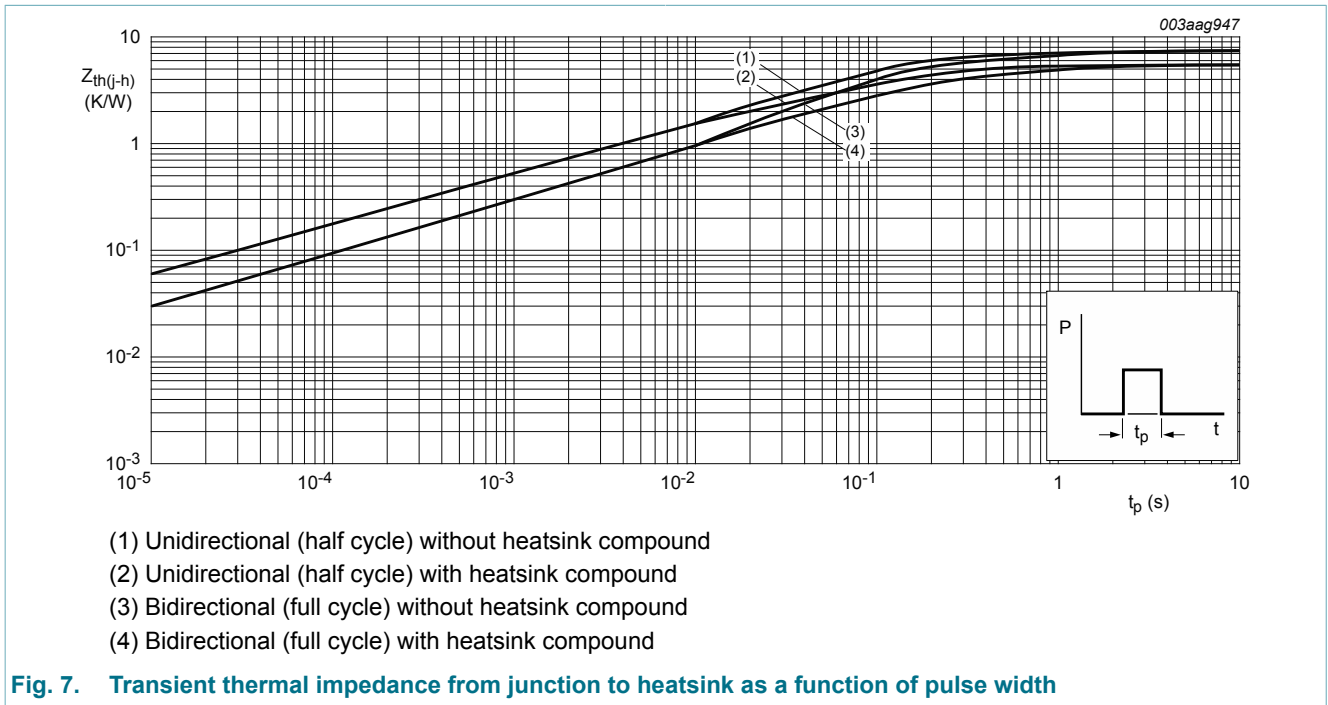


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; Fig. 7	-	-	5.5	K/W
		full cycle or half cycle; without heatsink compound; Fig. 7	-	-	7.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



### 9. Isolation characteristics

Table 6. Isolation characteristics

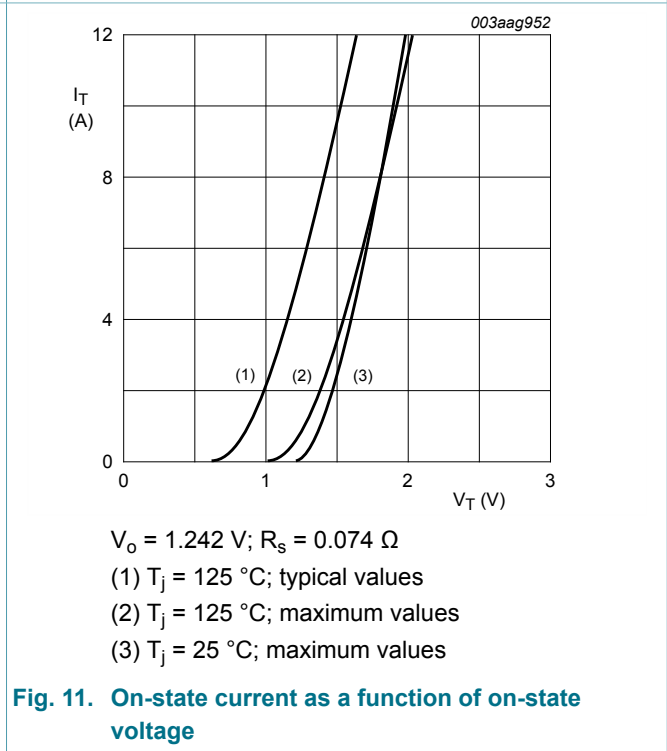
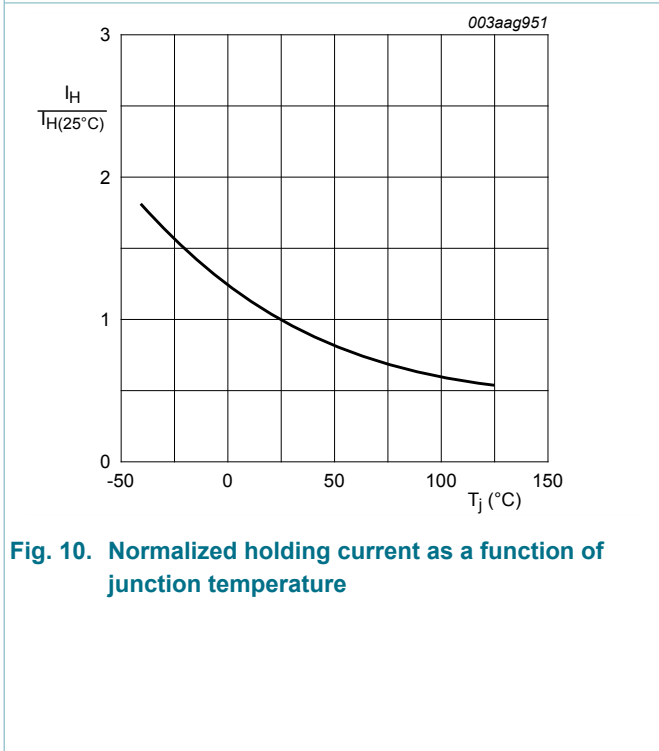
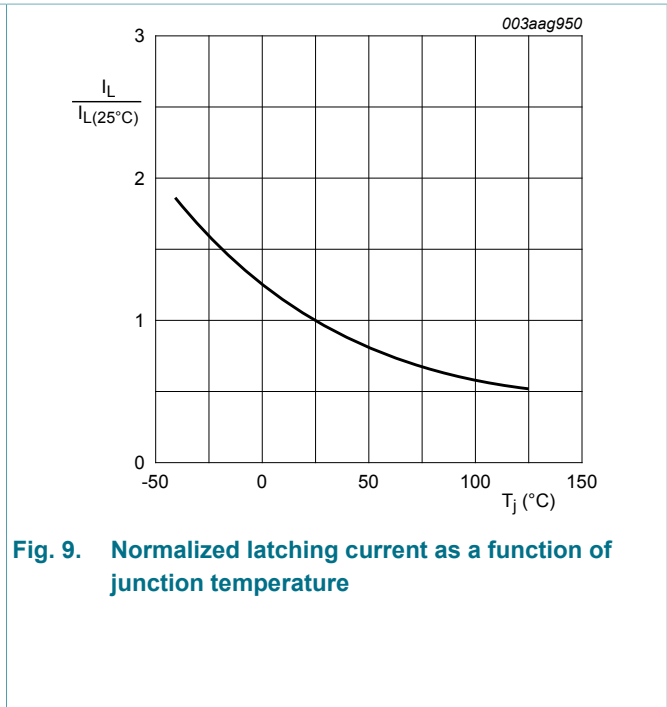
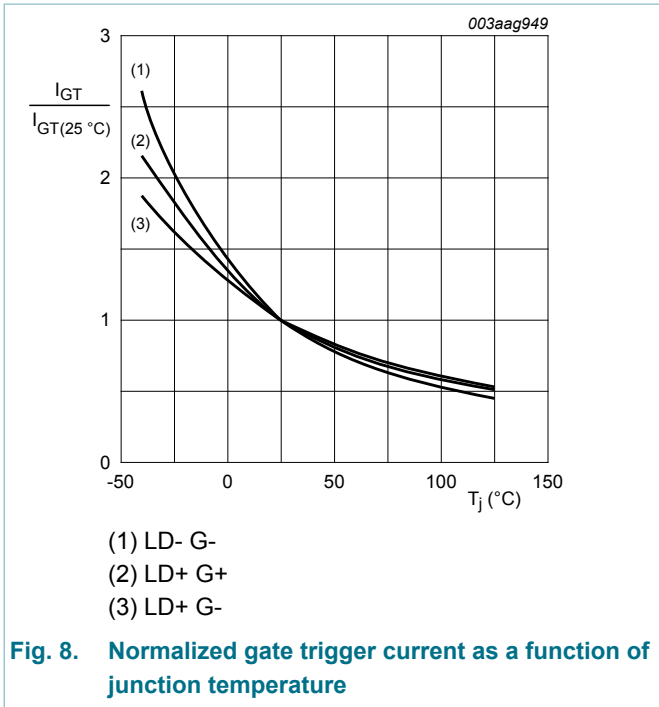
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65% RH; $T_h = 25\text{ °C}$ ; from all terminals to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
$C_{isol}$	isolation capacitance	f = 1 MHz; $T_h = 25\text{ °C}$ ; from main terminal 2 to external heatsink	-	10	-	pF

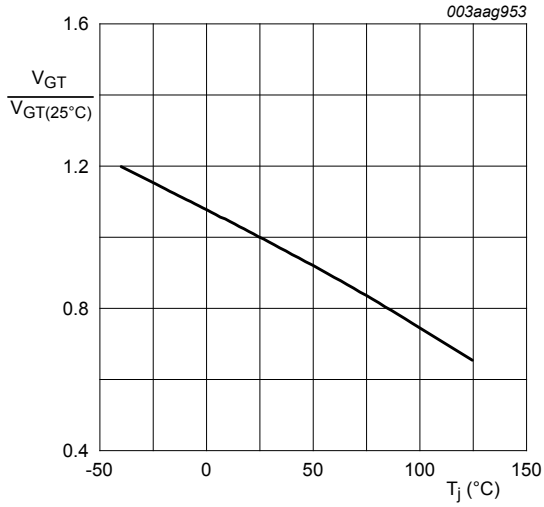
## 10. Characteristics

Table 7. Characteristics

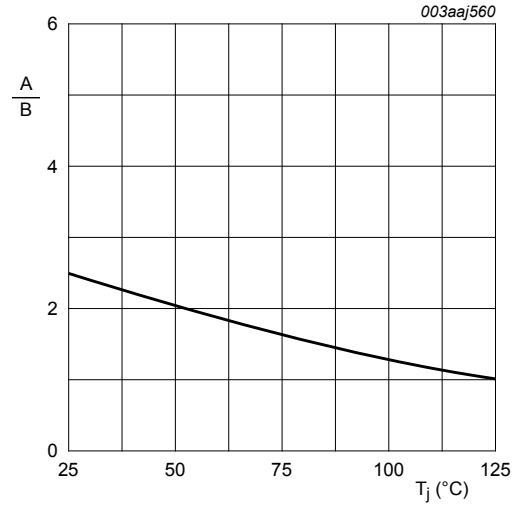
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	10	mA
I <sub>L</sub>	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	30	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	40	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	30	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 6 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>	-	-	1.7	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 125 °C; <a href="#">Fig. 12</a>	0.2	0.45	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 25 °C	-	-	10	µA
		V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>	500	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 20 V/µs; (snubberless condition); gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	4	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 10 V/µs; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	5	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	A/ms





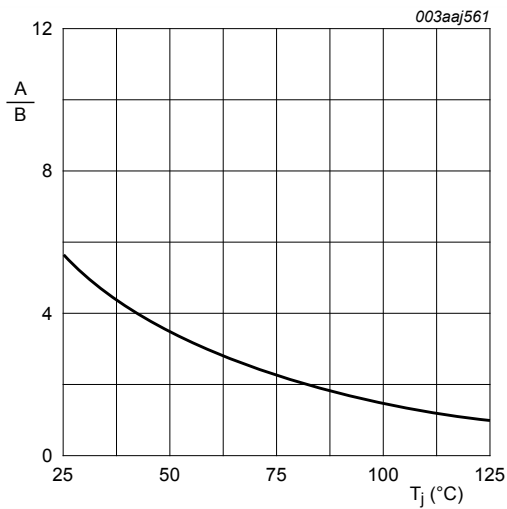


**Fig. 12. Normalized gate trigger voltage as a function of junction temperature**



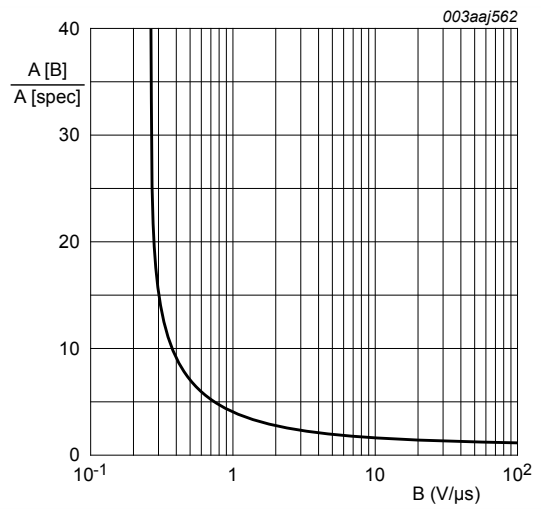
A =  $dV_D/dt$  at condition  $T_j$  °C  
 B =  $dV_D/dt$  at condition  $T_j$  [125] °C

**Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature**



A =  $di_{com}/dt$  at condition  $T_j$  °C  
 B =  $di_{com}/dt$  at condition  $T_j$  [125] °C  
 $V_D = 400$  V

**Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature**



A [B] is  $di_{com}/dt$  at condition B,  $dV_{com}/dt$   
 A [spec] is the specified data sheet value of  $di_{com}/dt$   
 turn-off time < 20 ms

**Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values**

### 11. Package outline

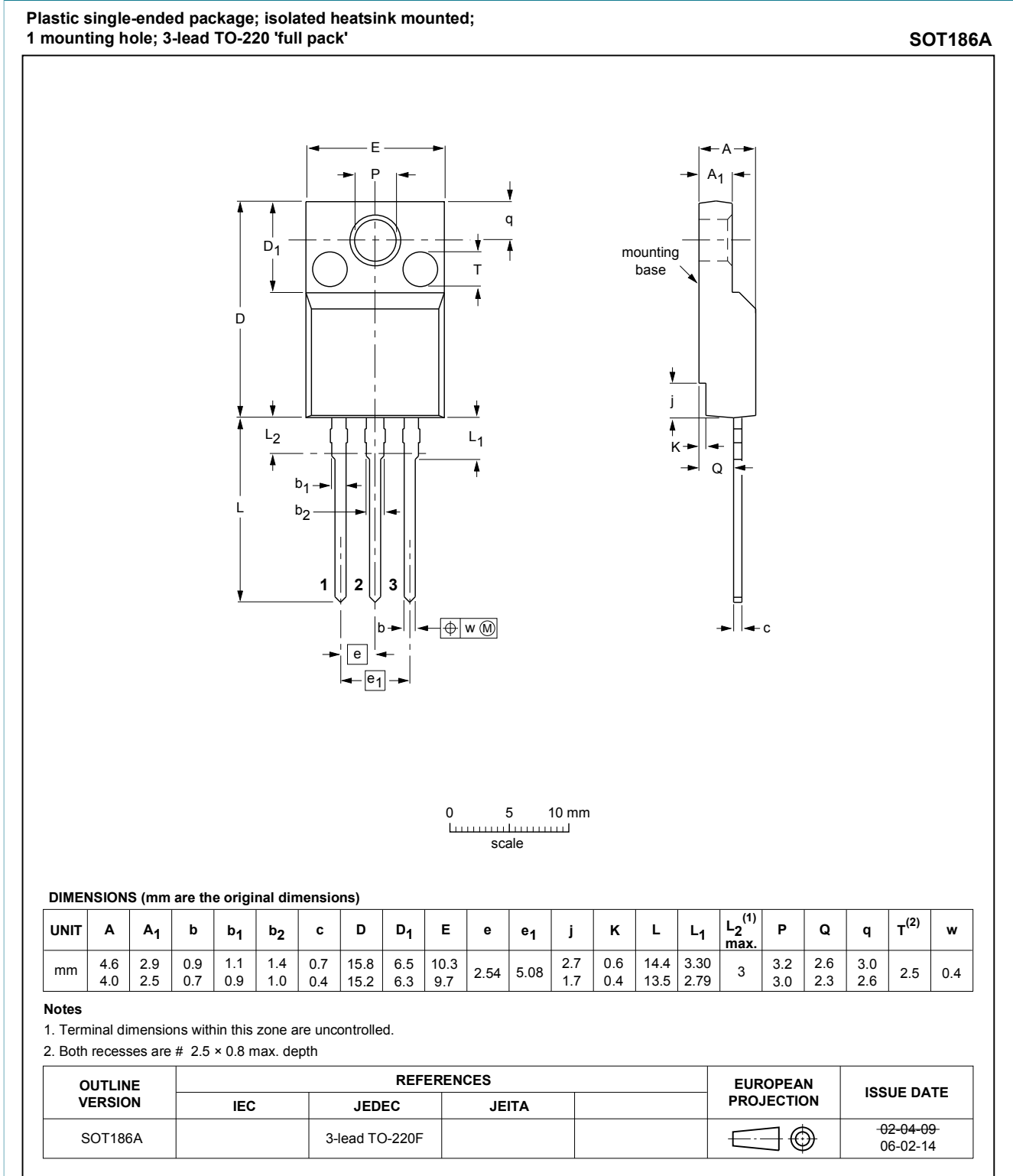


Fig. 16. Package outline TO-220F (SOT186A)

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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## 13. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Limiting values .....	3
8	Thermal characteristics .....	6
9	Isolation characteristics .....	6
10	Characteristics .....	7
11	Package outline .....	10
12	Legal information .....	11
12.1	Data sheet status .....	11
12.2	Definitions .....	11
12.3	Disclaimers .....	11
12.4	Trademarks .....	12

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